

MS2321

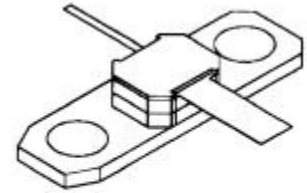
RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

Features

- DESIGNED FOR HIGH POWER PULSED IFF, DME, AND TACAN APPLICATIONS
- 20 W (typ.) IFF 1030–1090 MHz
- 15 W (min.) DME 1025–1150 MHz
- 15 W (typ.) TACAN 960–1215 MHz
- 1025 - 1150 MHz
- 50 VOLT OPERATION
- $P_{OUT} = 15$ WATTS
- $G_P = 10$ dB MINIMUM
- 20:1 VSWR CAPABILITY @ RATED CONDITIONS
- COMMON BASE CONFIGURATION

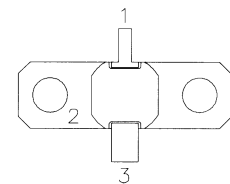
DESCRIPTION:

The MS2321 is a gold metallized, silicon NPN power transistor designed for pulsed applications with low duty cycles such as IFF, DME and TACAN. Internal impedance matching is utilized for maximum broadband performance and simplified external matching.



.250 SQ. 2LFL (M105)
hermetically sealed

PIN CONNECTION



1. Collector
2. Base
3. Emitter

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	65	V
V_{CEO}	Collector-Emitter Voltage	65	V
V_{EBO}	Emitter-Base Voltage	3.5	V
I_C	Device Current	1.5	A
P_{DISS}	Power Dissipation	87.5	W
T_J	Junction Temperature	+200	$^{\circ}C$
T_{STG}	Storage Temperature	-65 to +150	$^{\circ}C$

Thermal Data

$R_{TH(J-C)}$	Junction-case Thermal Resistance	2.0	$^{\circ}C/W$
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ELECTRICAL SPECIFICATIONS (Tcase = 25°C)
STATIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
BV_{CBO}	$I_C = 10mA$ $I_E = 0mA$	65	---	---	V
BV_{CES}	$I_C = 25mA$ $V_{BE} = 0V$	65	---	---	V
BV_{EBO}	$I_E = 1mA$ $I_C = 0mA$	3.5	---	---	V
I_{CES}	$V_{CE} = 50V$ $I_E = 0mA$	---	---	2	mA

DYNAMIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
P_{OUT}	$f = 1025 - 1150$ MHz $P_{IN} = 1.5W$ $V_{CC} = 50V$	15	---	---	W
G_P	$f = 1025 - 1150$ MHz $P_{IN} = 1.5W$ $V_{CC} = 50V$	10	---	---	dB
η_C	$f = 1025 - 1150$ MHz $P_{IN} = 1.5W$ $V_{CC} = 50V$	30	---	---	%

Conditions: Pulse Width = 10 μ Sec Duty Cycle = 1%

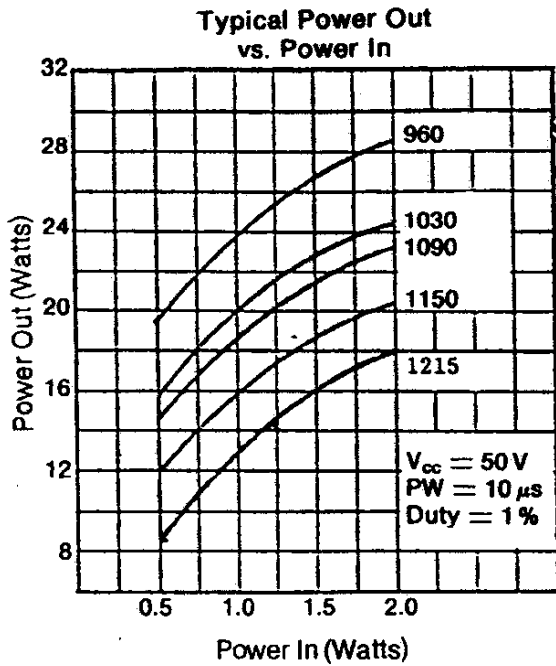
IMPEDANCE DATA

FREQ	$Z_{IN} (\Omega)$	$Z_{CL} (\Omega)$
1025 MHz	3.0 + j5.0	5.8 + j7.5
1090 MHz	3.8 + j7.5	3.3 + j8.5
1150 MHz	2.5 + j20.0	6.0 + j8.9

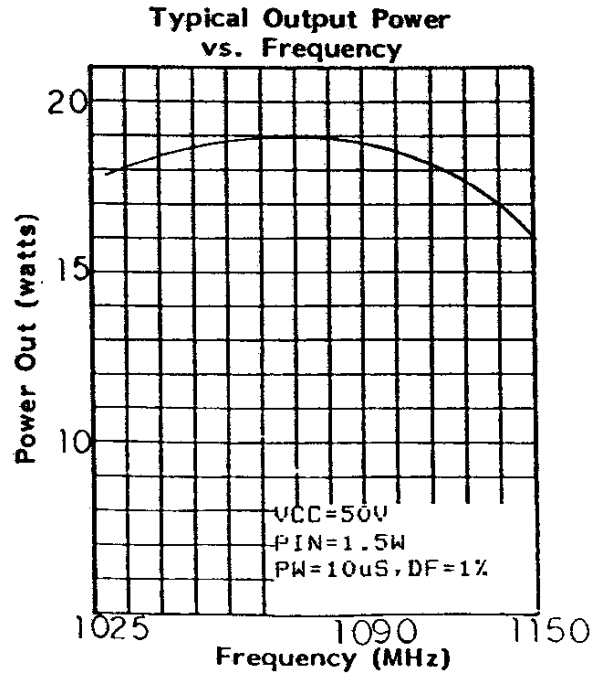
$V_{CC} = 50V$
 $P_{IN} = 1.5W$

TYPICAL PERFORMANCE

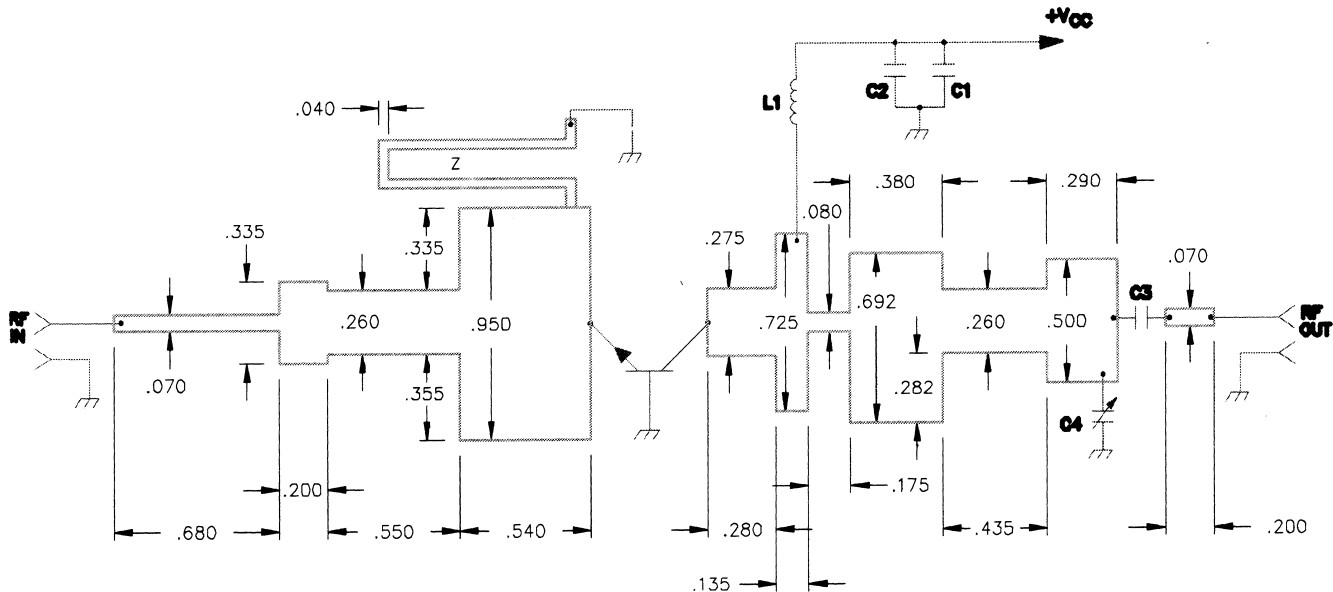
POWER OUTPUT vs POWER INPUT



POWER OUTPUT vs FREQUENCY



TEST CIRCUIT



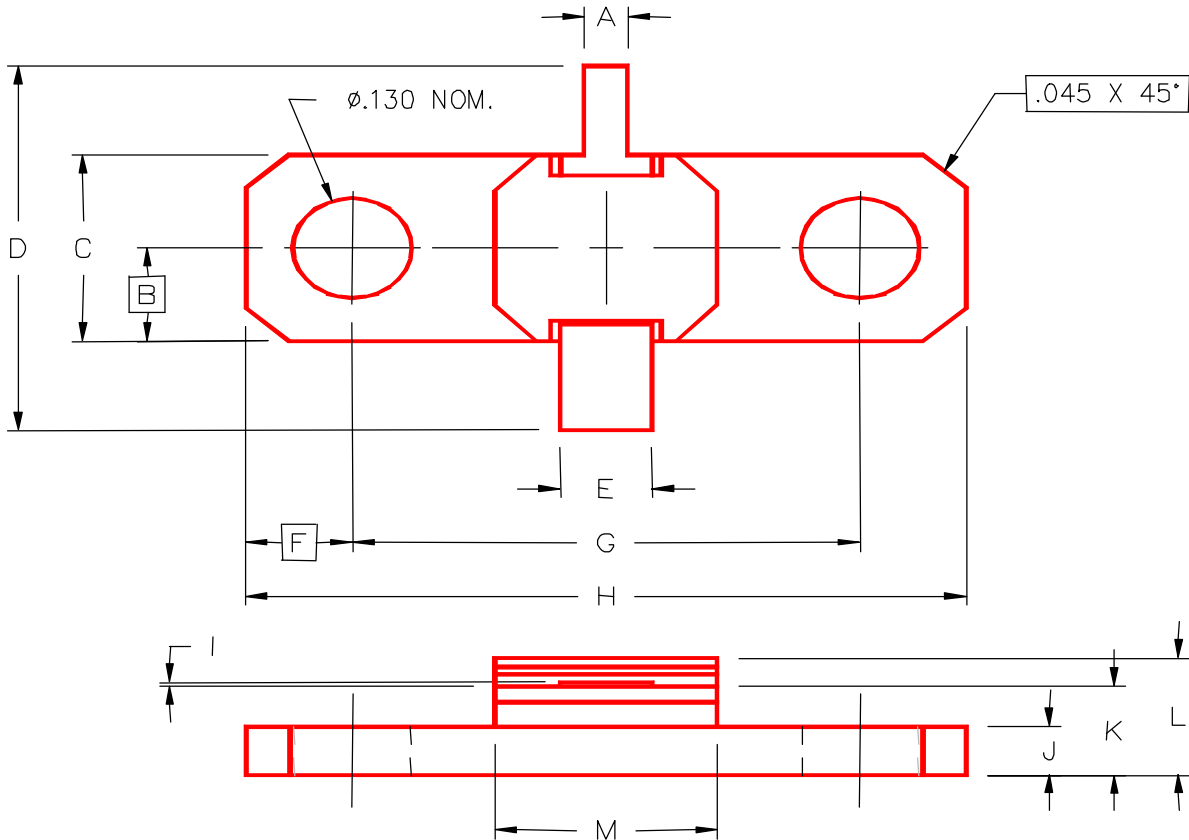
- C1 : 1000 μ F Electrolytic
- C2 : 680pF Chip Capacitor
- C3 : 120pF Chip Capacitor
- C4 : 0.6 - 4.5pF Johanson Gigatrim

- L1 : 6 1/2 Turns, #22 AWG on a #30 Drill Bit
- Z : Printed Transmission Line, Length = 1.91"

- Board : Er = 2.5, .034" Thick
- All Dimensions are in Inches.

PACKAGE MECHANICAL DATA

PACKAGE STYLE M105



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.045/1,14	.055/1,40	I	.002/0,05	.006/0,15
B	.125/3,18		J	.057/1,45	.067/1,70
C	.245/6,22	.255/6,48	K	.112/2,84	.132/3,35
D	1.235/31,37		L		.175/4,45
E	.095/2,41	.105/2,67	M	.245/6,48	.405/10,29
F	.120/3,05				
G	.557/14,15	.567/14,40			
H	.795/20,19	.805/20,45			

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